

Vacuum Systems Lecture 4

V. Baglin CERN TE-VSC, Geneva





Vacuum, Surfaces & Coatings Group Technology Department

Outline

- 1. Synchrotron radiation and photodesorption
- 2. Vacuum instability and ion stimulated desorption
 - 3. Particle losses and ion stimulated desorption
 - 4. Electron cloud and related surface parameters



1. Synchrotron radiation and photodesorption

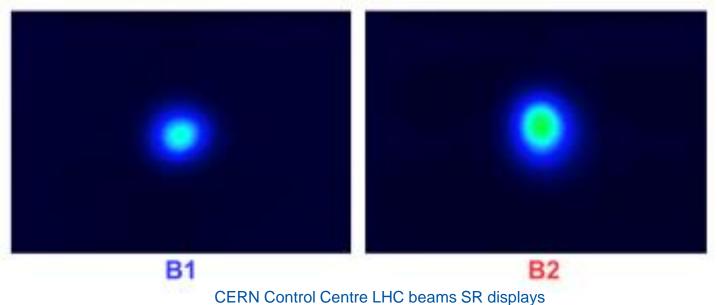


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Synchrotron radiation: visible light

In synchrotron, particles can radiate light by synchrotron radiation
Can be use for diagnostics purposes :

LHC SYNCHROTRON LIGHT MONITORS



- But particles loose energy by synchrotron radiation → should be compensated by RF system
- Beam emittance shrink by synchrotron radiation
- Power is dissipated on the machine elements
- Molecules are desorbed from the vacuum chamber wall due to synchrotron radiation

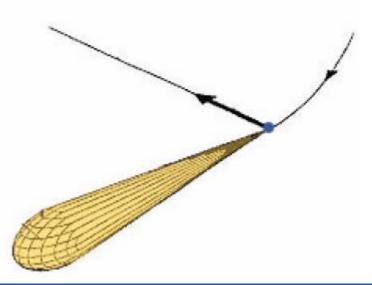


Synchrotron Radiation

- A charged particle which is accelerated produce radiation
- The power of the centripetal radiation is larger than the longitudinal radiation (factor γ^3)
- For a relativistic particle, the radiation is highly peaked (opening angle ~ $1/\gamma$)
- The radiation energy range from infra-red to gamma rays: from meV to MeV

References :

K. Hübner, CAS 1984, CERN 85-19
R.P. Walker, CAS 1992, CERN 94-01
A. Hofmann, CAS 1996, CERN 98-04
L. Rivkin, CAS 2008





Critical energy

• The critical energy split the <u>power spectrum</u> in two equals parts

$$\varepsilon_c = \frac{3}{2} \frac{\text{hc}}{2\pi} \frac{\gamma^3}{\rho}$$

Electrons:
$$\varepsilon_c [eV] = 2.21810^3 \frac{E[GeV]^3}{\rho[m]}$$

Protons: $\varepsilon_c [eV] = 3.583510^{-7} \frac{E[GeV]^3}{\rho[m]}$

- 90 % of the emitted photons have an energy lower than the critical energy
- Magnetic rigidity:

$$B \rho = \frac{p}{e} \approx \frac{E}{e c} \qquad \frac{1}{\rho} \approx \frac{3}{10} \frac{B[T]}{E[GeV]} \qquad \qquad \mathcal{E}_c \propto \frac{E^3}{\rho} \propto B E^2$$



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Dissipated power

• The energy emitted by the synchrotron radiation per turn and per particle is:

$$\Delta E = \frac{\mathrm{e}^2}{3\varepsilon_0} \frac{\gamma^4}{\rho} = \frac{4\pi}{3} r \,\mathrm{m}_0 \mathrm{c}^2 \frac{\gamma^4}{\rho}$$

with $r = \frac{1}{4\pi\varepsilon_0} \frac{e^2}{m_0 c^2}$ (classical radius)

• The average power emitted per turn by the beam is:

$$P_{tour} = \Delta E \frac{N}{t} = \frac{e \gamma^4}{3\pi \varepsilon_0 \rho} I$$

• So, the average power emitted by the beam per unit of length is:

$$P_0 = \frac{\partial P}{\partial s} = \frac{e \gamma^4}{6\pi\varepsilon_0 \rho^2} I$$

$$P_0 \propto \frac{E^4}{\rho^2} I \propto B^2 E^2 I$$



Dissipated power

• The average power emitted by the beam per unit of length is

$$P_0 [W/m] = \frac{e}{3\varepsilon_0 (m_0 c^2)^4} \frac{E^4}{2\pi\rho^2} I$$

$$\mathbf{P}_0 \propto \frac{\mathbf{E}^4}{\rho^2} \mathbf{I} \propto \mathbf{B}^2 \mathbf{E}^2 \mathbf{I}$$

• Electrons :

• Protons:

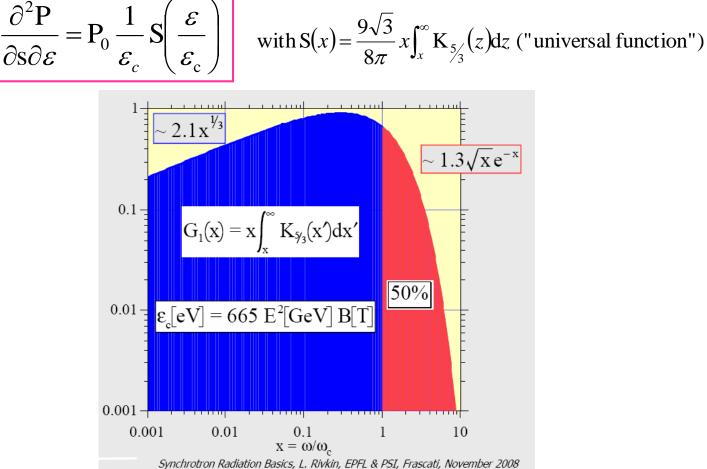
$$P_0 [W/m] = 88.57 \frac{E[GeV]^4}{2\pi \rho[m]^2} I[mA] \qquad P_0 [W/m] = 7.79 \, 10^{-12} \frac{E[GeV]^4}{2\pi \rho[m]^2} I[mA]$$



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Power spectrum

- The SR power emitted by a particle is a function of the vertical angle and the wavelength.
- Integrating over the vertical angle, one obtains the spectral power density per unit of length : $2^2 \mathbf{p} = 1$





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Photon flux

- Since the photon flux is linked to the power by : $P = \Gamma \varepsilon$
- The photon flux per unit length in a relative energy band is written:

$$\frac{\partial \Gamma}{\partial \varepsilon / \varepsilon} = \frac{\partial^2 P}{\partial s \partial \varepsilon} = P_0 \frac{1}{\varepsilon_c} S\left(\frac{\varepsilon}{\varepsilon_c}\right)$$

• So, the total photon flux per unit of length is:

$$\mathbf{\hat{\Gamma}} = \int_{0}^{\infty} \frac{\partial \Gamma}{\partial \varepsilon} d\varepsilon = \frac{P_{0}}{\varepsilon_{c}} \times \int_{0}^{\infty} \left(\frac{\varepsilon}{\varepsilon_{c}}\right)^{-1} S\left(\frac{\varepsilon}{\varepsilon_{c}}\right) d\left(\frac{\varepsilon}{\varepsilon_{c}}\right) = \frac{15\sqrt{3}}{8} \frac{P_{0}}{\varepsilon_{c}} = \frac{5\sqrt{3}e}{12 \text{ h } \varepsilon_{0}c} \frac{\gamma}{\rho} I$$

$$\mathbf{\hat{\Gamma}} \propto \frac{E}{\rho} I \propto B I$$



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Linear photon flux

• The photon flux per unit of length is given by :

$$\overset{\bullet}{\Gamma} = \frac{15\sqrt{3}}{8} \frac{P_0}{\varepsilon_c} = \frac{5\sqrt{3}e}{12 \text{ h } \varepsilon_0 \text{ c }} \frac{\gamma}{\rho} \text{ I}$$

$$\dot{\Gamma} \propto \frac{E}{\rho} I \propto B I$$

• Electrons :

• Protons:

•

$$\Gamma$$
[photons.m⁻¹.s⁻¹] = 1.28810¹⁷ $\frac{\text{E[GeV]}}{\rho[\text{m}]}$ I[mA]

•

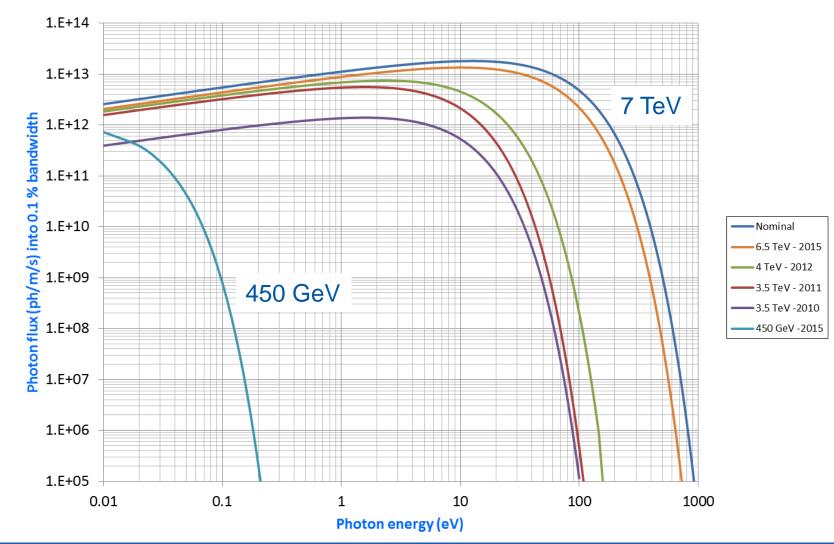
$$\Gamma$$
[photons.m⁻¹.s⁻¹] = 7.01710¹³ $\frac{E[GeV]}{\rho[m]}$ I[mA]



LHC SR Spectrum : from IR to UV

With nominal parameters : 7 TeV and 585 mA
2010, 2011, 2012 and 2015 spectra

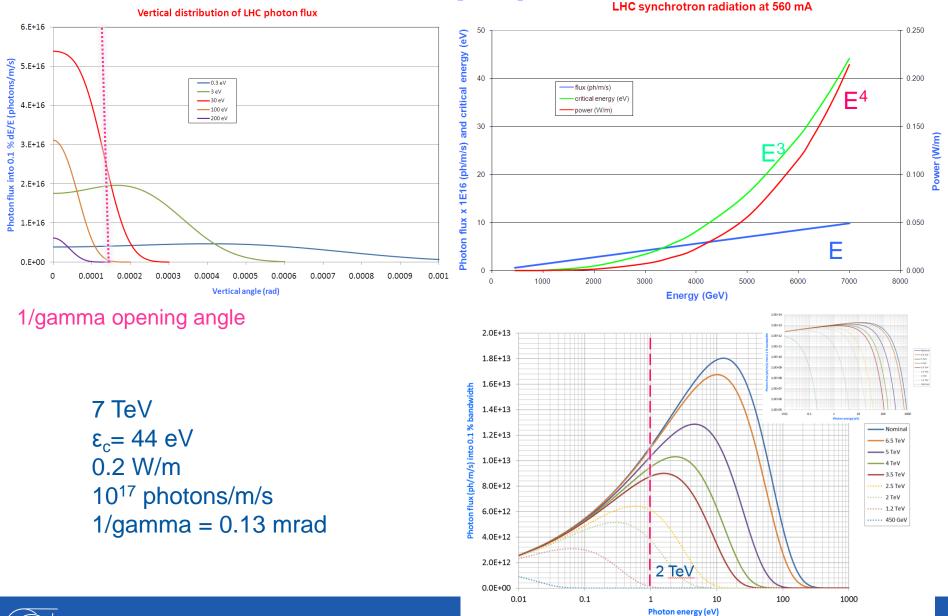
Key parameter: photodesorption yield





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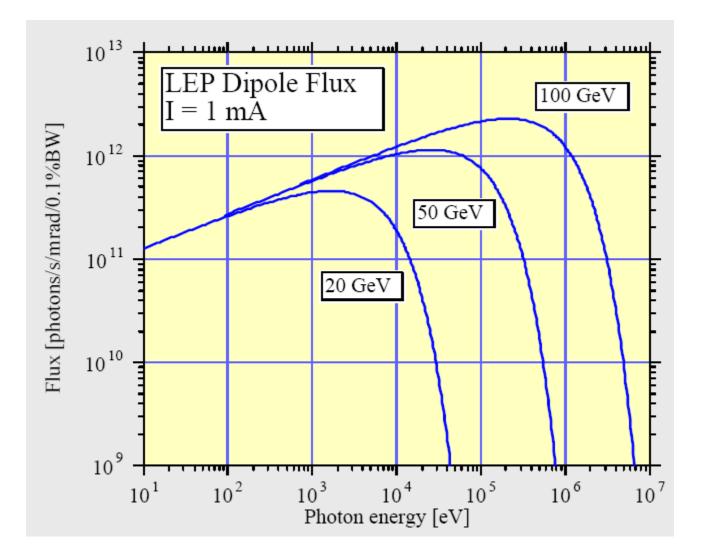
LHC SR properties





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LEP SR spectrum: X-rays & gamma rays





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Parameter impact on different type of machines ...

		Soleil	KEK-B		LEP			LHC	
			LER	HER	Inj.	1	2	lnj.	Col.
Particle		e⁻	e+	e	e	e⁻	e⁻	р	р
Beam current	mA	500	2600	1100	3	3	7	584	584
Energy	GeV	2.75	3.5	8	20	50	96	450	7000
Bending radius	m	5.36	16.31	104.46	2962.96		2784.302		
Power	W/m	4 030	20 675	5 820	0.8	30	955	0	0.2
Critical energy	eV	8 600	5 800	11 000	6 000	94 000	660 000	0	44
Photon flux	photons/m/s	3 10 ¹⁹	(7 10 ¹⁹)	1 10 ¹⁹	3 10 ¹⁵	7 10 ¹⁵	3 10 ¹⁶	7 10 ¹⁵	(1 1017)
Dose at 3000 h	photons/m	4 10 ²⁶	8 10 ²⁶	1 10 ²⁶	3 10 ²²	7 10 ²²	3 10 ²³	7 10 ²²	1 10 ²⁴

• In LEP, and all synchrotron light sources, the evacuation of the power is an issue

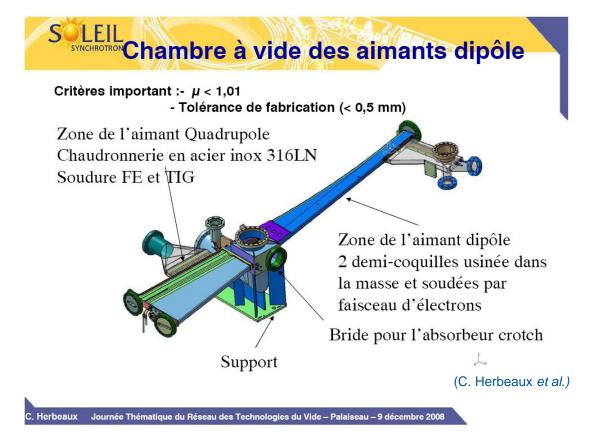
The LHC will operate at 7 TeV with ~ .6 A. Power evacuation is an issue for the cryogenic system (1 kW/arc !!)

• The critical energy varies from a few 10 eV to 660 keV. Strongly bound molecules can be desorbed

- The photon flux is large, so large gas load. Adequate dimensioning of the effective pumping speed
- The annual photon dose is large. Implications on gas reduction and radiation



- Stainless steel
- NEG coated, in-situ baked to 180°C



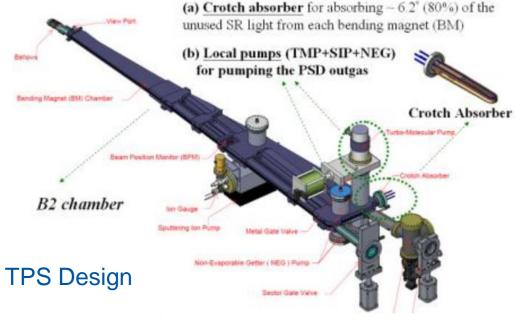
• A complex vacuum chamber design with a light extraction path, pumping and instrumentation ports and power absorbers (crotch)



Complementary information

- Extruded Aluminum
- Ex-situ baked to 150°C

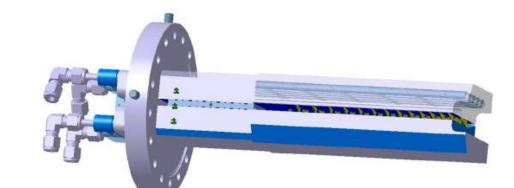


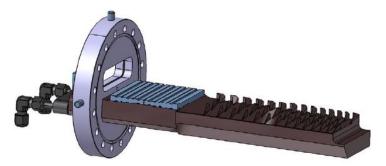


G.Y Hsiung et al.

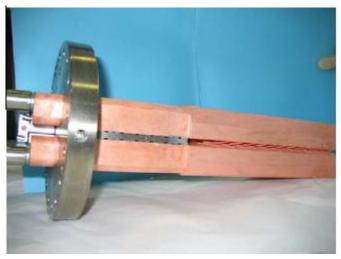
• A complex vacuum chamber design with a light extraction path, pumping and instrumentation ports and power absorbers (crotch)







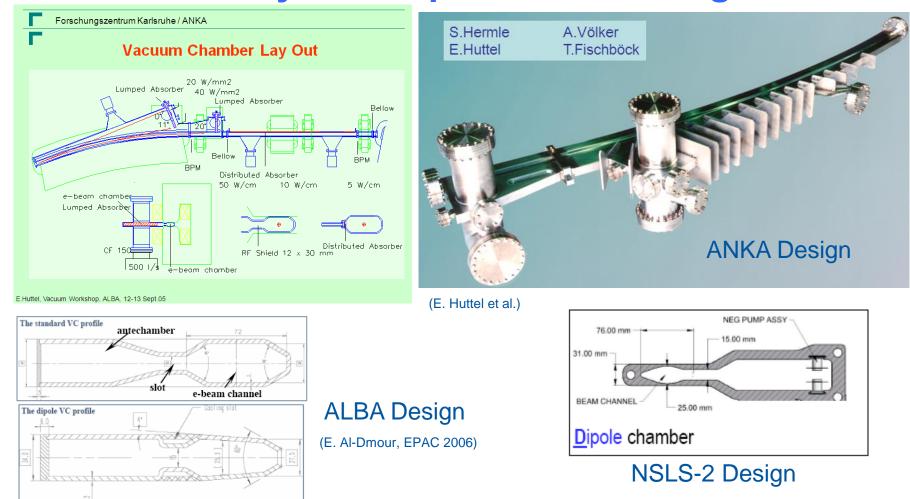
SOLEIL Design



(C. Herbeaux et al.)

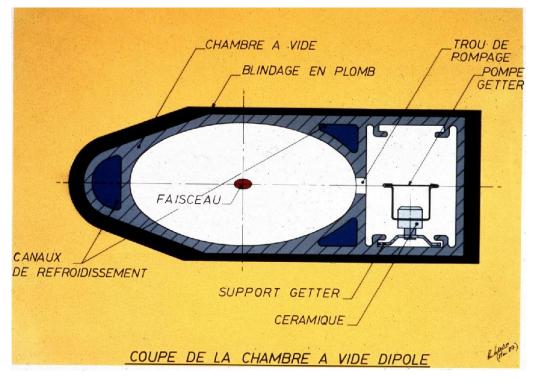
• Soleil « crotch » power absorber: Water cooled copper Glidcop (256 W/mm²)

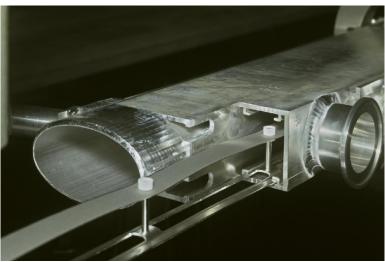




• Antechamber design to absorb the SR power externally to the beam path with the integration of a distributed pumping







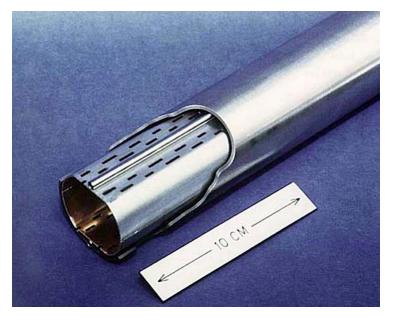
LEP Design

(CERN LEP Vacuum group)

• Antechamber and distributed NEG pumping, water cooling and lead shielding



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Courtesy N. Kos CERN TE/VSC



Courtesy N. Kos CERN TE/VSC

LHC Design

(CERN LHC Vacuum group)

 Perforated Cu colaminated beam screen to intercept the SR power protecting the 1.9 K cold bore and to allow a distributed pumping



Photodesorption

 The interaction of photons (light) with matters produce the desorption of neutral gases inside the vacuum system

• The photon stimulated desorption (PSD) of physisorbed (meV) or chemisorbed (eV) molecules can be direct or non-direct

• The identified transmitter are photoelectrons, secondary electrons and phonons

• The photon stimulate molecular desorption is a function of the nature of the material, its temperature, its surface state, of the photon energy and irradiation angle.

• No model exists, therefore *in-situ* qualification of material is required for the design of a future machine.



Photodesorption: current understanding

• The photodesorption process is linked to the production of photoelectrons and secondary electrons

- Photoelectrons contribute to the gas load by ESD
- The oxide and carbon layers are believed to be the source of gas

• The diffusion of atoms into the solid and their recombination at the surface plays a role

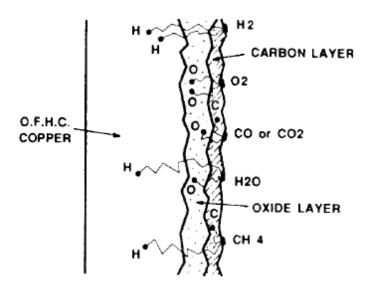
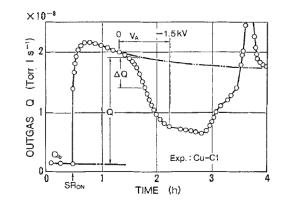
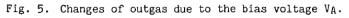


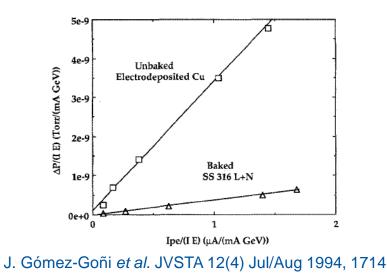
Fig. 6. Tentative Microscopic Model for PSD from OFHC Copper.

O. Gröbner et. al. EPAC 1992





T. Kobari *et al* Proc .of Vacuum Design of Synch Light Sources Conference, Argonne, 1990

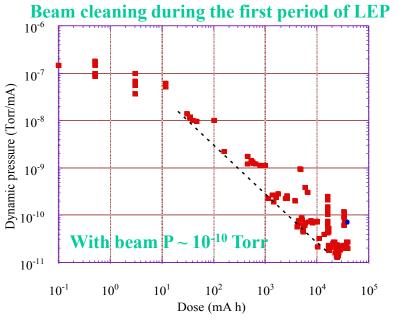




Dynamic pressure due to PSD

- The dynamic pressure decrease by several orders of magnitude with photon dose: "photon conditioning"
- The photon desorption yield is characterised by η_{photon}

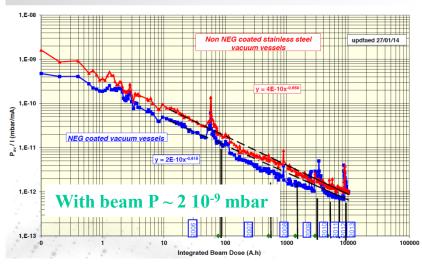
$$P = \frac{Q + \eta_{Photons} \mathring{\Gamma}_{Photons}}{S}$$



O. Gröbner. Vacuum 43 (1992) 27-30

SOLEIL





C. Herbeaux, Journée thématiques RTVide, décembre 2014

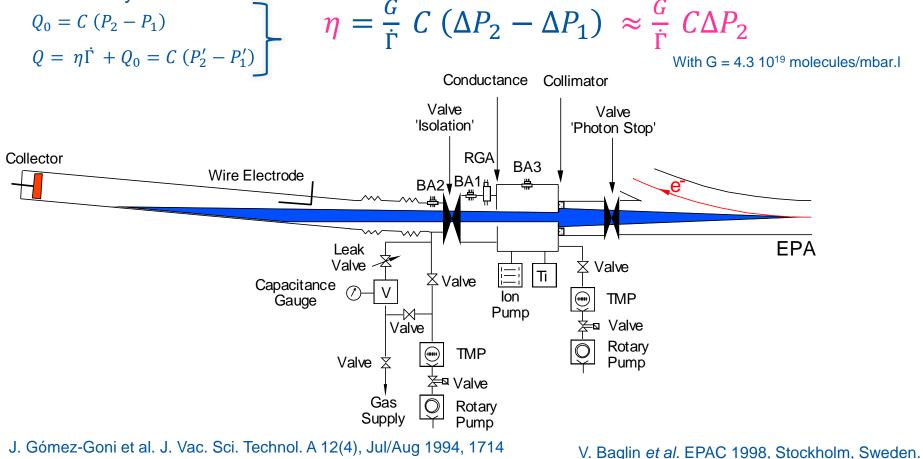


Photo-desorption yield measurement

• SR light is extracted from a dipole magnet to irradiate the chamber at ~ 11 mrad

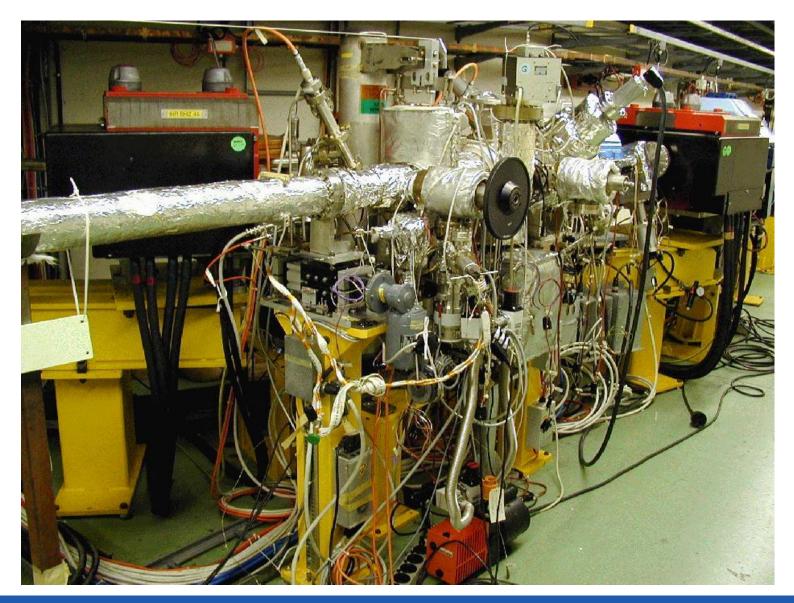
- SR fan is vertically collimated therefore photon flux < 4 eV are attenuated
- The gas load is measured by the throughput method via a conductance (72.5 l/s for N_2)

• A wire and a collector are biased for current measurement to estimate the photon reflectivity and photoelectron yield





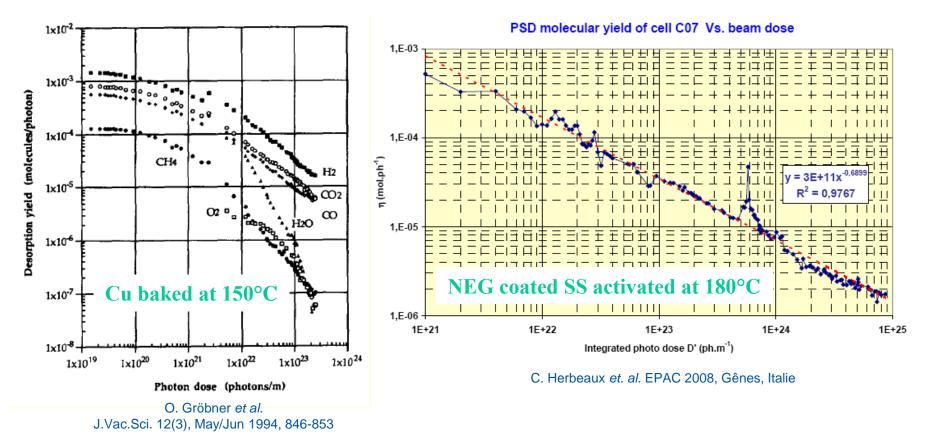
EPA Synchrotron Light Facility 42 - 1999





Conditioning under photon irradiation

• Typical desorption yield range: from 10⁻³ molecule/photon to 10⁻⁶ when conditioned



$$\eta_{Photons} = \eta_0 \left(\frac{\mathrm{D}}{\mathrm{D}_0}\right)^{-a}$$

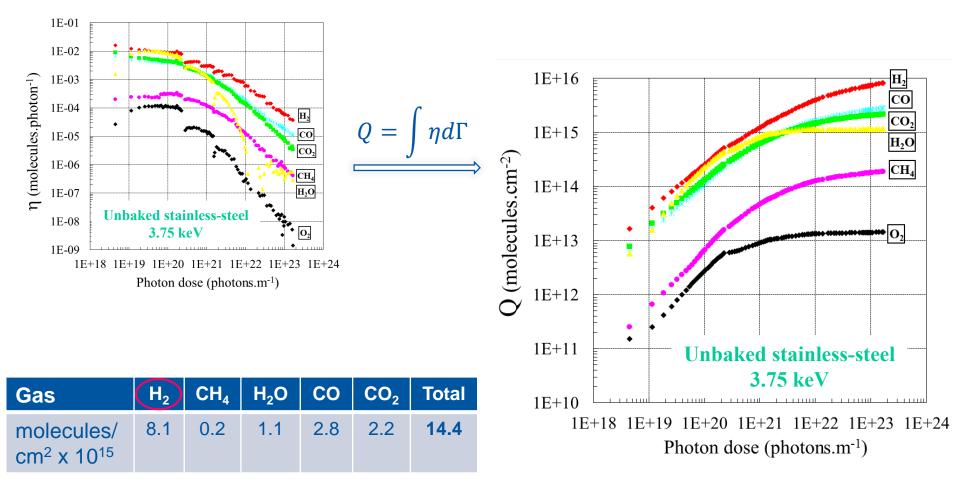
• The hydrogen desorption is characterised by a diffusion process: a = 0,5 M. Andritschky *et al.*, Vacuum 38 (8-10), 933, (1988)



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Gas load

• The total desorbed quantity amounts to 15 monolayers for an unbaked system



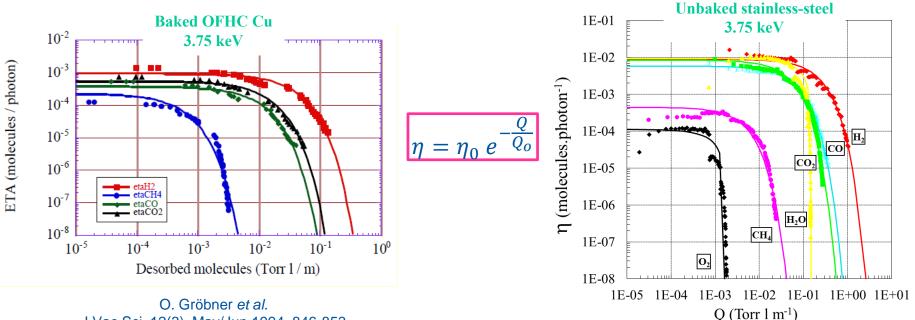
C. Herbeaux et al. JVSTA 17(2) Mar/Apr 1999, 635



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Desorption yield vs gas load

• The quantity removed during the cleaning process is a useful information to estimate intervals between getter reactivation or surface coverage on a cryogenic surface



J.Vac.Sci. 12(3), May/Jun 1994, 846-853

	H ₂	CH ₄	СО	CO ₂
η_0 (molecules/ph)	9.2 10 ⁻⁴	2.3 10-4	3.7 10-4	5.5 10 ⁻⁴
Q _o (Torr I /m)	3.0 10 ⁻²	4.5 10-4	8.4 10 ⁻³	1.1 10 ⁻²
Q ₀ (molecules/cm ²)	2.3 10 ¹⁴	3.5 10 ¹²	6.5 10 ¹³	8.5 10 ¹³

C. Herbeaux et al. JVSTA 17(2) Mar/Apr 1999, 635

H ₂	CH₄	СО	CO ₂
8.8 10 ⁻³	4.4 10-4	5.7 10 ⁻³	8.4 10 ⁻³
1.9 10 ⁻¹	3.9 10 ⁻³	5.7 10 ⁻²	4.0 10 ⁻²
1.5 10 ¹⁵	3.1 10 ¹³	4.5 10 ¹⁴	3.2 10 ¹⁴



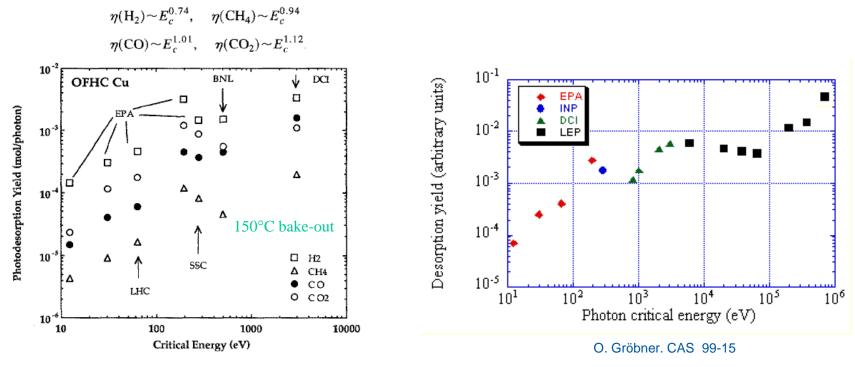
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Joint Universities Accelerator School, Archamps, February, 2017

Complementary information

Evolution with critical energy

- At low energy, the photoelectric effect dominates
- Above a few 100 keV, Compton diffusion dominates and produce a cascade of energetic recoil electrons with a diffusion of secondary photons



J. Gómez-Goñi et al. JVSTA 12(4) Jul/Aug 1994, 1714



Photodesorption of NEG films

- Very low desorption yields
- Be aware of the difference between effective and intrinsic yields

 $\eta_{intrisic} \simeq S \times \eta_{effective}$

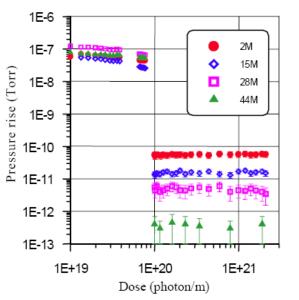


Figure 2: Pressure rise measured in the centre of the TiZrV coated test chamber before activation ($<1.10^{20}$ photons/m) and after activation ($>1.10^{20}$ photons/m).

TiZrV film on stainless-steel 4.5 keV

V. Anashin et al. EPAC 2002, Paris, France.

Table 1: Summary of results from the non-activated test chamber

Gas	Sticking probability	Photodesorption yield (molecules/photon)
H_2	0	1.10-3
CH4	0	2.5.10-4
CO	0	5.10-4
CO ₂	0	3.10-4

Baked at 80°C

Table 2: Summary of results from the activated test chamber

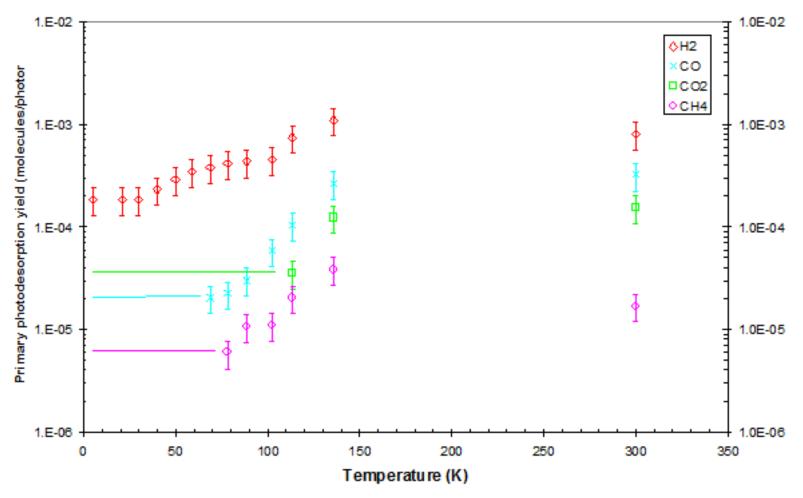
Gas	Sticking probability	Photodesorption yield (molecules/photon)		
H ₂	~0.007	~1.5.10 ⁻⁵		
CH_4	0	2.10-7		
CO (28)	0.5	<1.10-5		
C _x H _y (28)	0	<3.10-8		
CO ₂	0.5	<2.10-6		

Activated at 190°C



Photodesorption at Cryogenic Temperature

• Initial yield, η_0 , are smaller than at room temperature



V. Baglin et al., Vacuum 67 (2002) 421-428



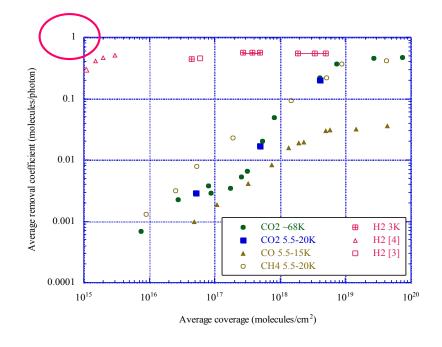
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What about physisorbed molecules?

1.0E-08

• Desorption of physisorbed molecules

Photo-cracking of molecules



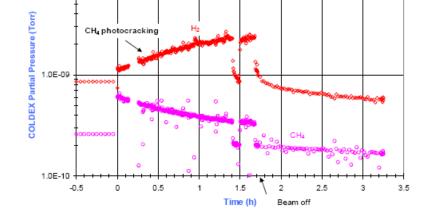
V. Anashin et al., Vacuum 53 (1-2), 269, (1999)

Stainless steel 250-300 eV Perpendicular incidence



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V. Baglin et al. EPAC 2002, Paris, France.



2. Vacuum instability and ion stimulated desorption

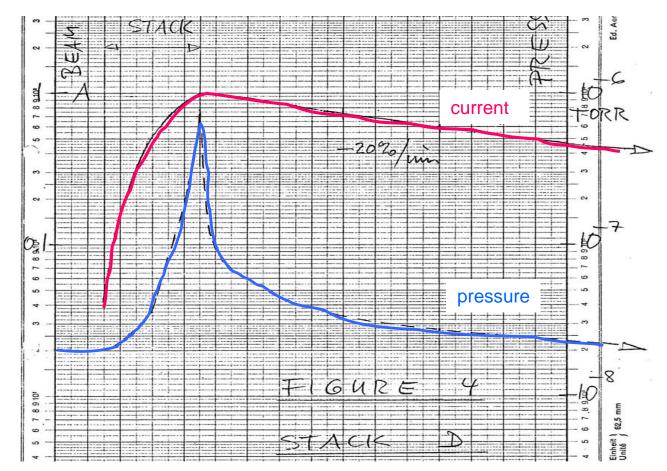


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The phenomenon

• High current machines: ISR, LHC ...

- Beam current increase to 1 A
- Pressure increase up to 10⁻⁶ Torr (x 50 en une minute)
- Beam loss



First documented pressure bump in the ISR

E. Fischer/O. Gröbner/E. Jones 18/11/1970



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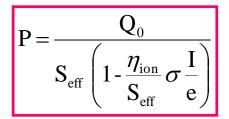
The mechanism of vacuum instability

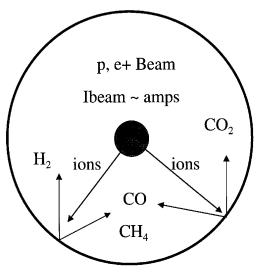
• Origin are ions produced by beam gas ionisation

$$V\frac{dP}{dt} = Q_0 + \eta_{ion}\sigma\frac{I}{e}P + C\frac{d^2P}{dx^2}$$



$$Q_0 + \eta_{ion} \sigma \frac{I}{e} P = P S_{eff}$$





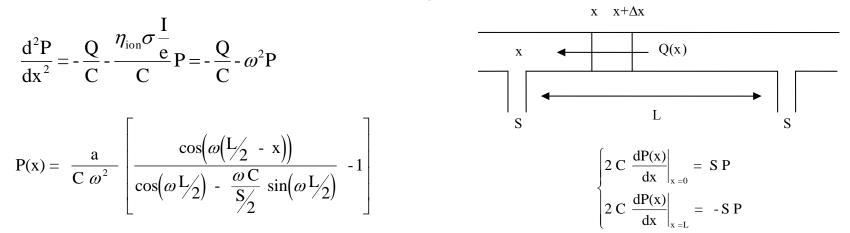
• When the beam current approach the critical current, the pressure increases to infinity

$$(\eta_{\rm ion} I)_{\rm crit} = \frac{e S_{\rm eff}}{\sigma}$$



Description of the mechanism

• In the case of a machine with distributed pumping $(C \neq 0)$:



• When the denominator approach zero, the pressure diverge

$$\cos\left(\omega \frac{L}{2}\right) - \frac{\omega C}{S_{2}} \sin\left(\omega \frac{L}{2}\right) > 0 \Leftrightarrow \omega \tan\left(\omega \frac{L}{2}\right) < \frac{S}{C} \Rightarrow \left(\omega \frac{L}{2}\right) < \frac{\pi}{2}$$
so $\eta_{ion} I < \frac{\pi^{2} C e}{410^{3} (\frac{L}{2}) \sigma}$ therefore $\left(\eta_{ion} I\right)_{crit} = \frac{\pi^{2} C e}{410^{3} (\frac{L}{2}) \sigma}$

• In the case of more complex geometry, numerical tools are used



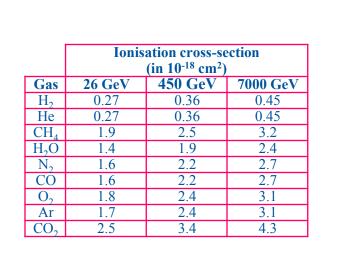
Ionisation cross section

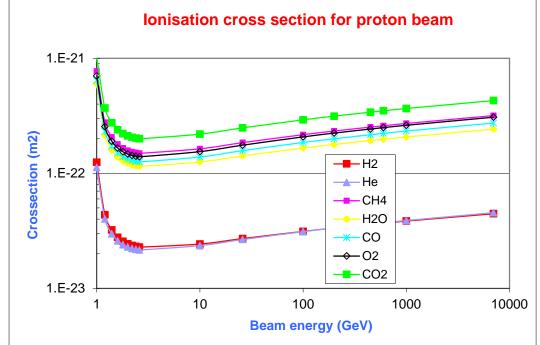
Complementary information

 It is a function of the speed & the charge of the projectile and of the nature of the residual gas.

$$\sigma = 4\pi \left(\frac{h/2\pi}{m_{e}c}\right)^{2} \frac{Z^{2}}{\beta^{2}} \left[M^{2} \left(\ln \left(\frac{\beta^{2}}{1-\beta^{2}}\right) - \beta^{2}\right) + C\right]$$

F.F. Rieke, W. Prepejchal , Phys. Rev. A5, 1507 (1972)





Heavy gas must be avoided

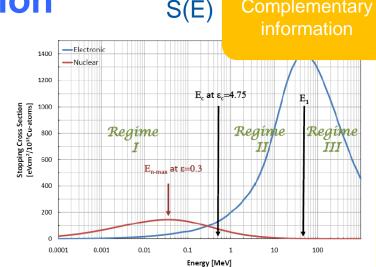


Ion desorption

 Described by the nuclear and electronic stopping force (stopping power)

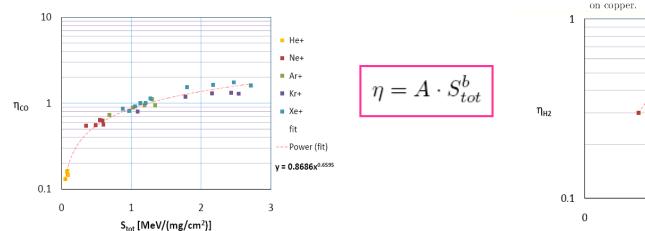
• Low masses (H₂) are desorbed by the electronic energy transfer to the lattice

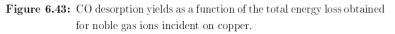
 High masses are desorbed by the direct nuclear momentum transfer between two particles



Complementary

Figure 4.3: Electronic and nuclear stopping cross sections for Ar⁺-ions incident





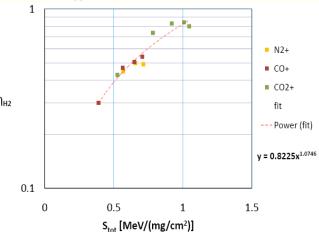


Figure 6.48: H₂ desorption yields as a function of the total energy loss obtained for N₂⁺-ions and oxygen containing ions incident on copper.

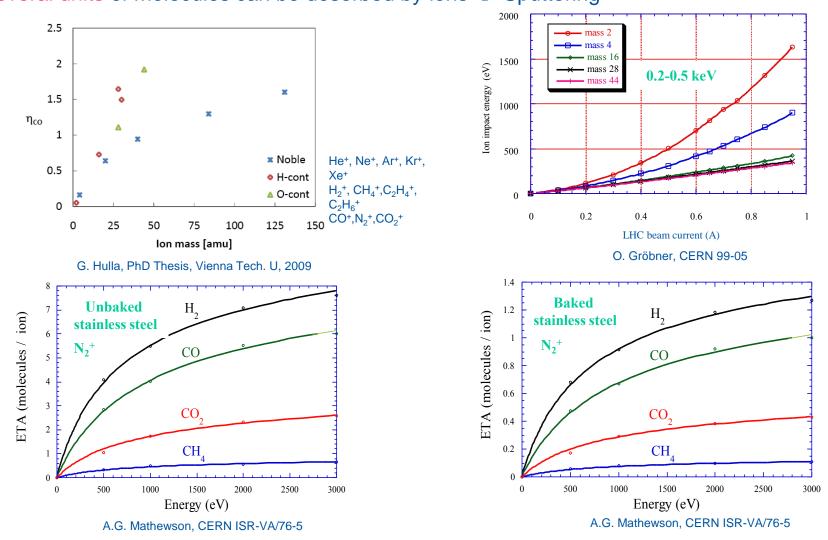
G. Hulla, PhD Thesis, Vienna Tech. U, 2009



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Ion desorption yield

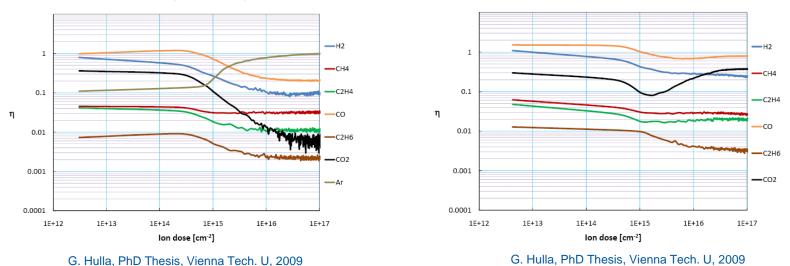
Varies with the material, the ion energy and ion species
Several units of molecules can be desorbed by ions -> Sputtering





Conditioning and implantation

• A conditioning is observed but at high dose, some ions can be implanted !



7 keV, Cu Baked, Ar⁺

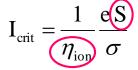
7 keV, Cu Baked, CO⁺

- In the LHC : the maximum flux is about 3 10⁸ ions/(cm².s) *i.e.* a dose of 3 10¹⁵ ions/(cm².year)
- In the LHC, there is no conditioning due to ion bombardment

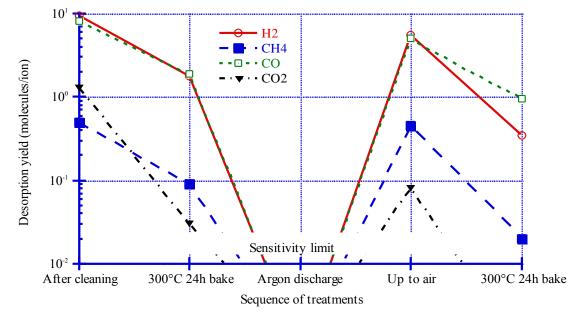


How to ensure vacuum stability ?

• Beam conditioning being negligible, one must decrease the desorption yield and optimise the pumping speed



• ISR : Argon glow discharge (Ar, 10 % O₂,~ 400 V, 10¹⁸ Ar/cm²)) with *in-situ* bakeout :



A.G. Mathewson, CERN ISR-VA/76-5



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At cryogenic temperature

H₂⁺, 3.2 K

1E+15

1E+16

1E+17

Taux de couverture (molécules.cm⁻²)

(N. Hilleret, R. Calder, IVC, 1977)

 $\eta'_{H2} \sim 2000$

 $\eta'_{CO2} \sim 2$

@ 5 keV and 1 monolayer

1E+18

1E+05

Coefficient de désorption (molécules.ion⁻¹) ⁺³ ⁺³

> 1E+02 + 1E+14

Complementary information

→ 0.5 keV

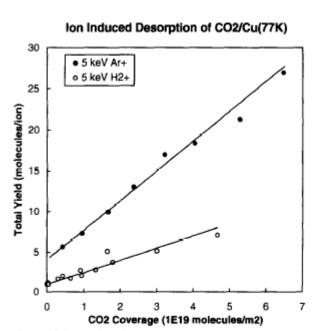
- 1 keV

- 5 keV

1E+19

10 keV

1E+20



Desorption of physisorbed gas

Figure 2. Total desorption yields from adsorbed $CO_2/Cu(77K)$ induced by bombardment of 5 keV H_2^+ and Ar^+ ions, plotted as a function of CO_2 dose. The lines indicated are best fit lines drawn by eye through experimental points.

J. Barnard et al., Vacuum 47 (4), 347, (1996)

• Critical current is changed to $I_c = -$

•It is a function of the geometry, the gas specie, the sticking coefficient and of the 2 desorption

 $\frac{\alpha \,\mathrm{S}}{\left(\eta_{\mathrm{ion}} + \eta_{\mathrm{ion}}^{'}\right)\frac{\sigma}{a}}$



LHC beam screen stability

Complementary information

• A minimum pumping speed is provided beam the beam screen's holes

$$(\eta_i I)_{\text{crit}} = \frac{e}{\sigma} S_{\text{eff}}$$

	H ₂	CH ₄	CO	CO ₂
(<i>ηI</i>) _{crit} [A]	1300	80	70	35

• Beam screen's holes provide room for LHC upgrades



Courtesy N. Kos CERN TE/VSC

• NB : In the long straight sections, vacuum stability is provided by TiZrV films and ion pumps which are less than 28 m apart



Pressure increase in LHC due to ions ?

• The ion flux is a function of the pressure and the beam current

$$\Gamma_{\rm ion} = \sigma \frac{\rm I}{\rm e} \rm P \simeq 310^8 \ ions/cm^2/s = 310^{11} \ ions/m/s$$

• For nominal parameters, $P \sim 10^{-8}$ mbar and I ~ 600 mA

• Ion energy will be about 100 eV, so the desorption yield about 2 molecules/ion

$$Q = \frac{\eta \Gamma}{3.310^{19}} = 2 \ 10^{-8} \text{ mbar.} \ell/\text{s/m}$$

• Beam screen pumping speed, S

$$S = 3.63 \,\mathrm{A}\sqrt{\frac{\mathrm{T}}{M}} \cong 1000 \,\ell/\mathrm{s/m}$$

• Pressure increase due to ion:

$$\Delta \mathbf{P} = \frac{Q}{S} = 10^{-11} \,\mathrm{mbar}$$

→ No visible pressure increase in LHC



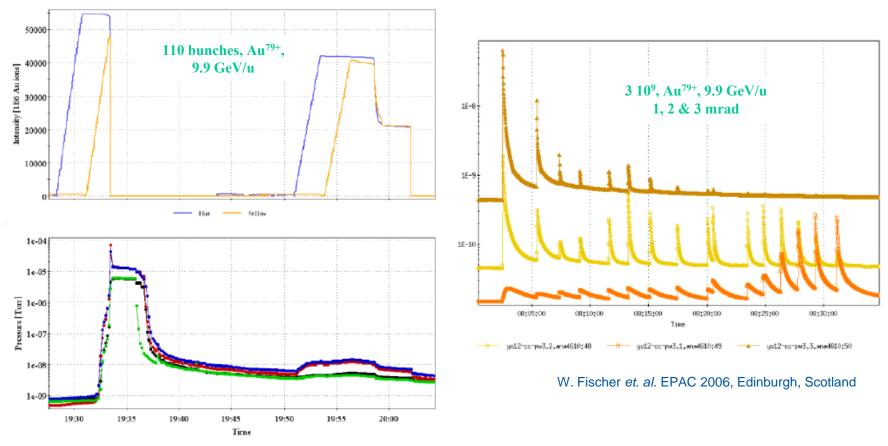
3. Particle losses and ion stimulated desorption



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RHIC

• Loss of ions from a beam leads to large pressure increases: 10⁻⁸ ...10⁻⁵ mbar!



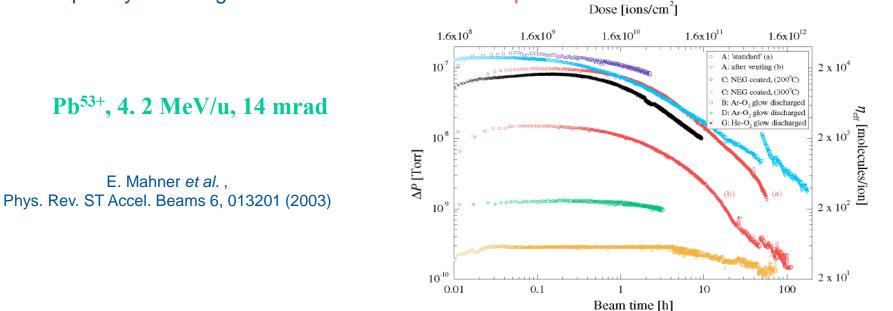
W. Fischer et. al. EPAC 2002, Paris, France



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High energy ions

• Desorption yields range from 20 – 20 000 molecules per ion



• The desorption is determined by the energy given to the electrons (electronic stopping force)



• The desorption induced by the electrons is the responsible mechanism



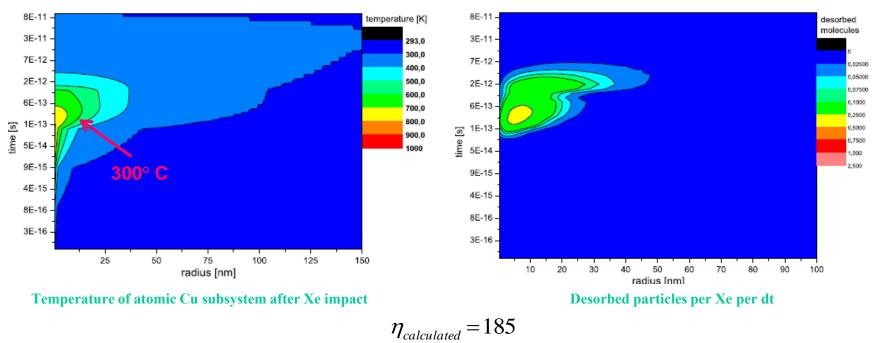
Mecanism

Complementary information

- Surface effect (except diffusion H₂) due to a thermal activation
- « Inelastic thermal spike model » : a temperature map coupled to the thermal desorption model

$$\eta = \int_0^{t_{max}} \int_0^{r_{max}} v_0(T(r,t)) \cdot \tilde{n}(r,t) \cdot \exp\left(-\frac{E_{des}}{k_B \cdot T(r,t)}\right) \cdot 2\pi \cdot r dr dt,$$

M. Bender et al., NIM B 267 (2007) 885-890



Xe²⁹⁺, 1.4 MeV/u, Perpendicular



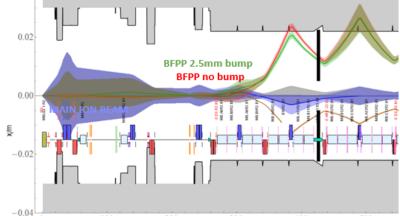
500

J. Jowett

Omet et. al. EPAC 2008, Genoa, Italy

information





s/m

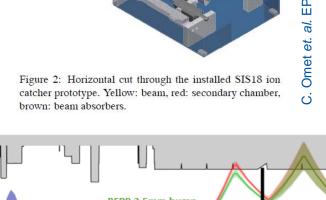
300

400

200

100

Joint Universities Accelerator School, Archamps, February, 2017



Remedies

- Use of NEG films (LEIR, RHIC, GSI)
- Use of beam conditioning
- Intercept ion loss on dedicated collimators:
 - LEIR : 30 µm gold fim on SS 316 LN, perpendic
 - GSI : 0.1 μm gold film, perpendicular incidence. Absorbeur inserted in a secondary vacuum chamber. NEG film

7 ZxTeV ions coming from BPFP

- HL-LHC : movable collimator – 150 W of

BFPP: $208Ph^{82+} + 208Ph^{82+} \rightarrow 208Ph^{82+} + 208Ph^{81+} + e^+$

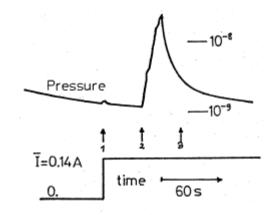
4. Electron cloud and related surface parameters



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History: observed at the ISR

- Vacuum stability test of a baked aluminium chamber 200°C, diam 160 mm (1976-1977)
- Observation of pressure spikes, particularly during transverse displacement of a proton bunch
- The existence of the spike varies with :
 - bunch length
 - number of proton bunch
- Existence of a current threshold (120 mA for 20 bunches)
- Different gas composition (dominated by H₂ instead of CO)
- Measurement of a significant electron current on the clearing electrodes
 - → Gas desorption is stimulated by electrons
 - Electrons are accelerated by the proton bunch: multipactor effect

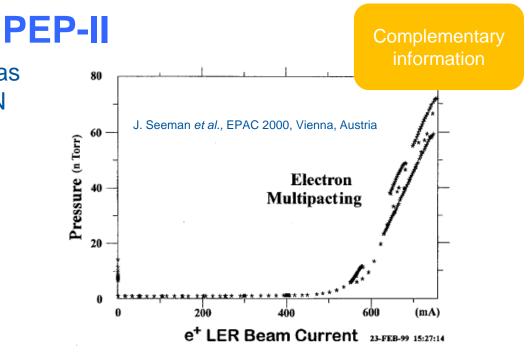


- Fig. 1. Pressure spike observed during slow displacement of a bunched beam across the aperture :
- 1 injection 40 mm, 2 10 mm and 3 + 10 mm radial position from centre of the vacuum chamber

O. Gröbner, ISR-VA/77-38



- Electron cloud in the positron ring was foreseen during the design phase: TiN coating on Aluminum
- emittance blow up above 800 mA (SR light)
- Observation of non linear pressure rise



- Winding of solenoids in the straight section
 - Luminosity increase





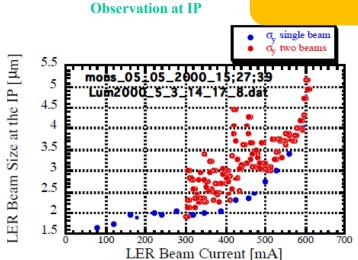
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Complementary information

- Cu OFHC vacuum chamber, unbaked, NEG pumping
- Emittance blow up in the vertical plane of the positron beam
- Positron bunch instability due to the cloud of photoelectrons
- Observed in multibunch mode

K. Ohmi, F. Zimmermann, PRL 85, 3821 (2000)

- Installation of permanent magnets then solenoids
 - Luminosity increase



Y. Funakoshi et al., EPAC 2000, Vienna, Austria



KEKB LER Solenoids



Stainless steel vacuum chamber baked at 250°C in the straight sections

- Stainless steel vacuum chamber cooled at 4 K in the arcs
- Pressure increase with protons and ions beams
- NEG, bakeout, solenoids, beam structure

Luminosity increase

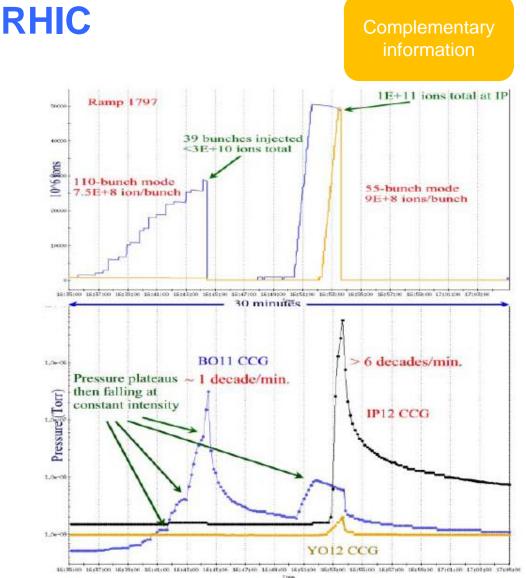


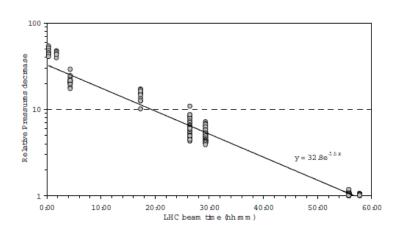
Fig 2. Pressure rises during 110-bunch and high intensity 55bunch mode Au operations. H. Hseuh *et al.*, EPAC 2002, Paris, France



- Unbaked stainless steel vacuum chamber
- Pressure increase observed with LHC type beams
- Measurement of electron current on a pick up

Ok for LHC beam injection

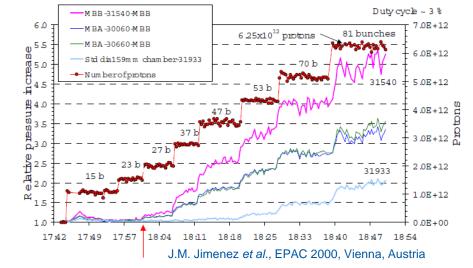
7.7 10¹⁰ protons/bunch





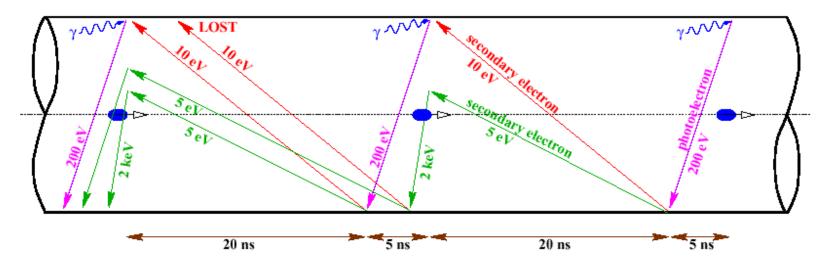
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SPS

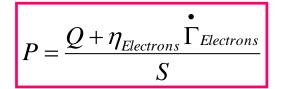
LHC mechanism



Schematic of electron-cloud build up in the LHC beam pipe.

F. Ruggiero et al., LHC Project Report 188 1998, EPAC 98

- Key parameters:
 - beam structure
 - bunch current
 - vacuum chamber dimension
 - secondary electron yield
 - photoelectron yield
 - electron and photon reflectivities





. . .

Simple model

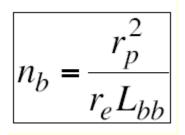
Synchronism condition:

$$\frac{2r_p}{\Delta v} \le t_{bb}$$

Speed increment due to the kick

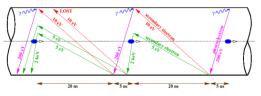
$$\Delta v = \frac{\Delta p}{m} = 2cr_e \frac{n_b}{r}$$

Intensity threshold:



• Enough energy gain due to the kick to produce secondaries:

$$\Delta W = \frac{\Delta p^2}{2m} = 2\frac{mc^2}{e}r_e^2 \left(\frac{n_b}{r}\right)^2$$



Schematic of electron-cloud build up in the LHC beam pipe.

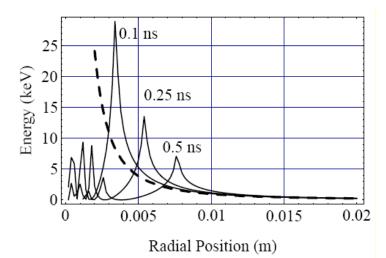


Figure: 1 Electron energy after the passage of a bunch in LHC versus the initial radial position for 0.1, 0.25 and 0.5 ns bunch length. The dotted curve is calculated for the stationary electron approximation.

O. Gröbner. PAC 97, Vancouver, Canada

Electrons in the vacuum chamber wall vicinity receive a kick of 190 eV, those in the beam vicinity receive 15 keV.



How to mitigate the electron cloud?

- Once again, play with the key parameters :
 - Reduce the photoelectron yield (grazing incidence has larger yield than perpendicular incidence)
 - Reduce the secondary electron yield (scrubbing, NEG or amorphous carbon films, geometry)
 - Reduce the amount of electrons in the system (solenoid magnetic field, clearing electrodes, material reflectivity)
 - Adapt the beam structure or the vacuum chamber dimensions to reduce the multiplication



. . .

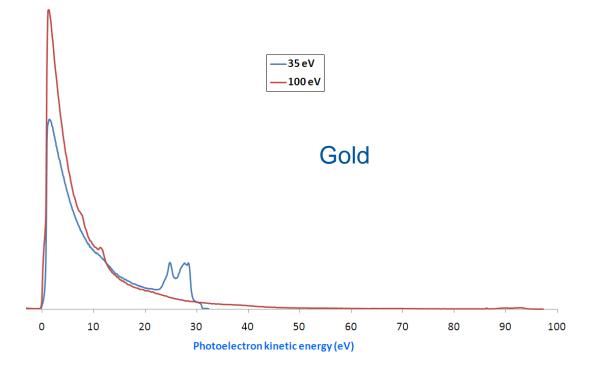
Photons from SR



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Photoelectrons

- Photoelectric effect : when a photons irradiates a surface with enough energy, it produces electrons
- The energy of emitted electrons varies from : 0 eV to $(hv-W_{\rm f}) \text{ eV}$
- Most of the electrons are secondaries
- A few 0.1 % to 1 % have high energy



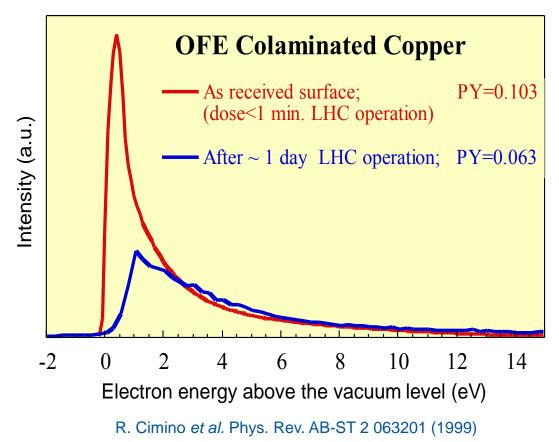
R. Cimino et al., Phys. Rev. ST Accel. Beams 2, 063201 (1999)



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EDC under SR irradiation

- EDC: Electron distribution curve
- SR dose reduce the amount of low energy photoelectrons
- The total yield is decreased by 40 % after 1 day of nominal LHC operation





Behaviour with critical energy

- SR irradiation at EPA
- Grazing incidence, 11 mrad
- The photoyield increases when increasing critical energy.
- Photon reflectivity slightly decreases when increasing critical energy
- PY*: photoelectrons per absorbed photons

		45 eV		194 eV	
Material	Status	R	PY*	R	PY*
Iviaterial		(%)	(e/ph)	(%)	(e/ph)
Al	unbaked	-	0.11	-	0.32
Cu-smooth	unbaked	81	0.11	77	0.32
Cu-	unbaked	5	0.08	7	0.08
electrodeposited	unbaked	5	0.08		0.00
Cu-sawtooth	unbaked	8	0.03	7	0.04
TiZr	unbaked	20	0.06	17	0.08
TiZr	activated	20	0.02	17	0.03
	at 350°C	20	0.02	1/	0.05

I.R. Collins et al. EPAC 1998, Stockholm, Sweden

NB : molecular desorption yields are linear in the range, 10 - 300 eV. So the photoelectron yield should be also proportional to critical energy

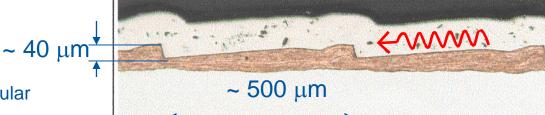
$$PY * \sim E_c$$



Photoelectrons for a LHC type beam screen

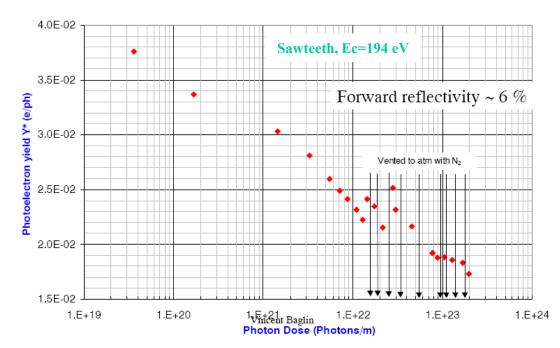
Complementary information

• The Photoyield decrease with **beam** conditioning



• It varies from 1 to 4 % under perpendicular incidence





V. Baglin et al., Chamonix, 2001

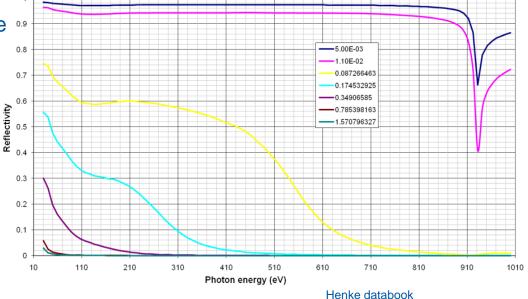


Photon reflectivity

- From 1 to 80% forward reflectivity
- Low reflectivity at perpendicular incidence ...
- High reflectivity at grazing incidence *i.e.* this is the case of SR in accelerators
- In LHC, 5 mrad gives more than 95% reflection
- Copper adsorption at 920 eV

		45 eV	194 eV	
Material	Status	R (%)	R (%)	
Cu roll	as-received	80.9	77.0	
bonded				
Cu roll	as-received	21.7	18.2	
bonded air				
baked				
Cu	as-received	5.0	6.9	
electroplated				
Cu sawtooth	as-received	1.8	-	
	150°C, 9 h	1.3	1.2	
	150°C, 24 h	1.3	1.2	
TiZr film	as-received	20.3	17.1	
	120°C, 12 h	19.5	16.7	
	250°C, 9 h	19.9	17.4	
	350°C, 10 h	20.6	16.9	
	CO saturated	20.7	-	

V. Baglin et al., Trieste, 1998



Copper reflection for unpolarised photon with 0 Angstreom roughness



O. Gröbner et al., 24-4-1988



Photon reflectivity of LHC type material

0.8

0.6

0.4

0.2 -

0.0

-50

0

50

θ,

Reflectivity

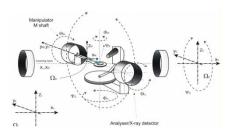
Complementary information

Saw tooth

100

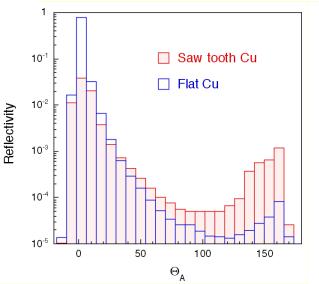
150

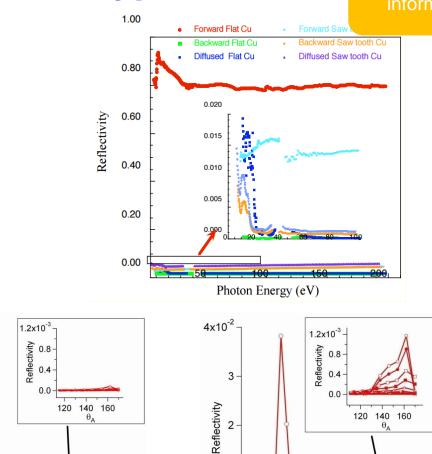
200



The saw tooth structure reduces the reflectivity

	Flat sample	Saw-tooth sample
Forward scattering	80 %	4 %
Back scattering	0 %	2 %
Diffused	2 %	4 %
Total	82 %	10 %





1

0

-50

0

50

 θ_A

N. Mahne *et al.* App. Surf. Sci. 235, 221-226, (2004)

200

150

Flat Cu

100



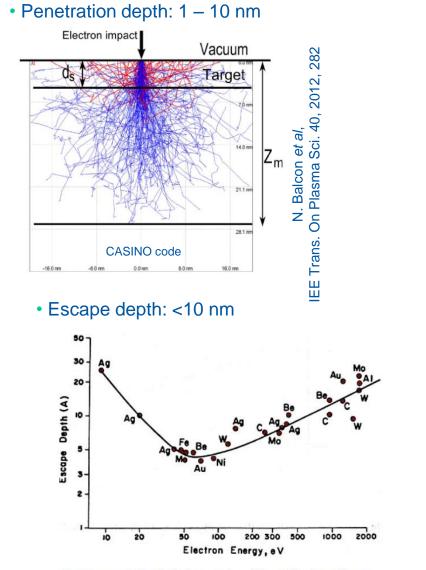
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Electrons from the electron cloud



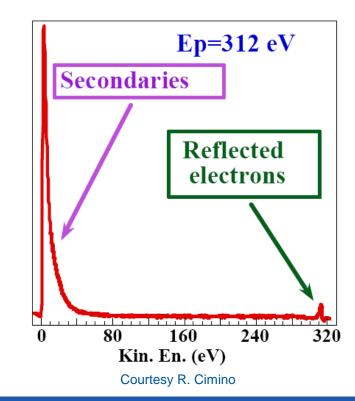
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Electron Distribution Curve (EDC)



• The electron distribution curve shows :

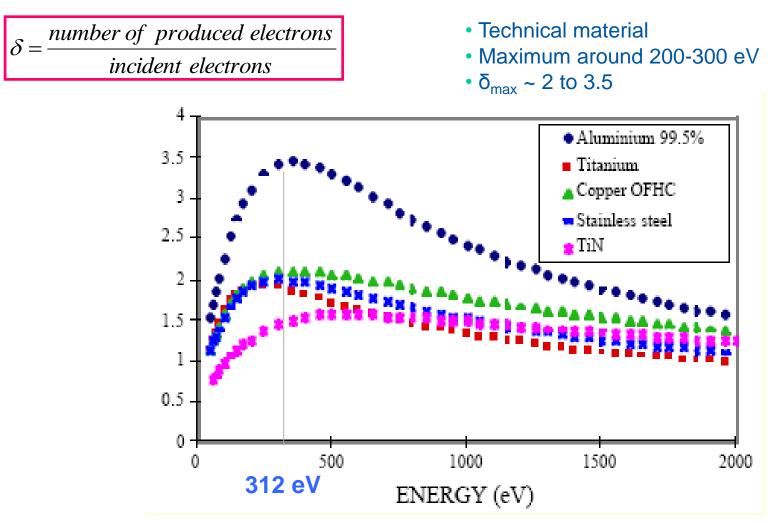
- Component at reflected electron energy
- Secondary electrons with low energy
- most of the emitted electrons have low energy



Mean escaped depth of electrons in solids and "universal" curve.



Secondary Electrons Curve



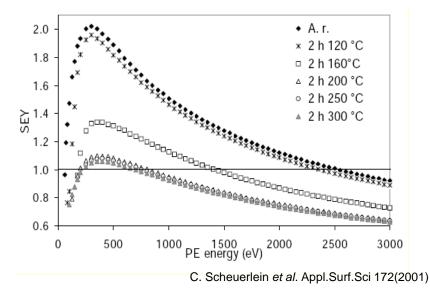
N. Hilleret et al., LHC Project Report 433 2000, EPAC 00



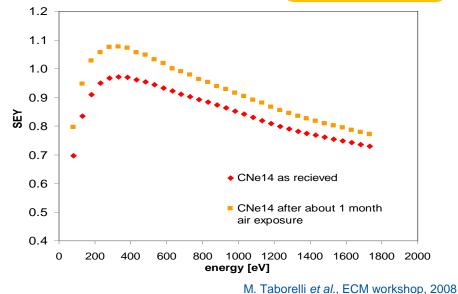
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Very low SEY

Complementary information



• TiZrV film



Amorphous carbon

The origin of the low SEY is different in both case :

- nature of the surface
- smooth versus rough surfaces

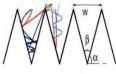


Geometrical effect

• Original idea with groove only:

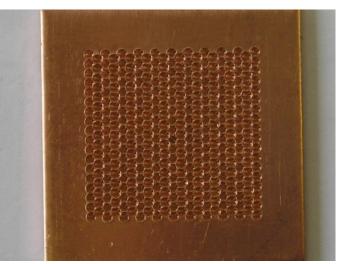
• After a coffee discussion, a drilled sampled by the VAC workshop (H. Kos)

• Ø ~1 mm , 92 holes/cm²

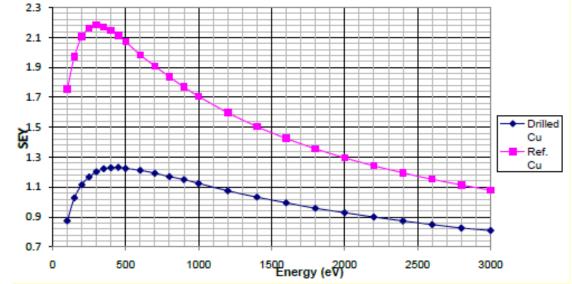


By A. Krasnov and By L Wang et.al

SEY max < 1.3 for Cu unbaked !!



Drilled Cu vs. air exposed Cu



Measurement courtesy A. Kuzucan

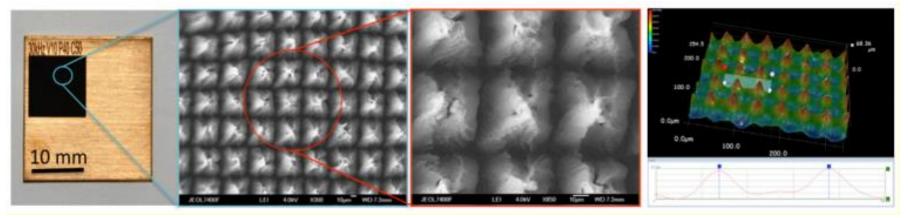
A fancy effect or a real application ?



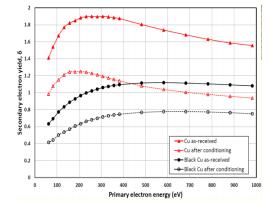
Laser Engineered Structure Surface

Complementary information

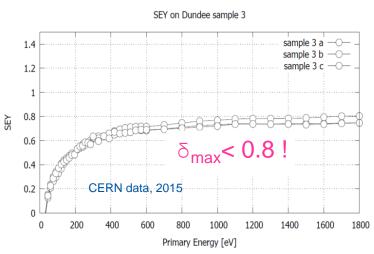
- Principle: laser treatment of a tube at atmospheric pressure
- Production of a micrometric structure



Appl. Phys. Lett. 101, 2319021 (2012). Physics Highlights – Physics Today (February 2013). Opt. Mater. Exp. 1,1425 (2011).



Applied Physics Letters 12/2014; 105(23): 231605

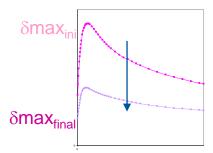


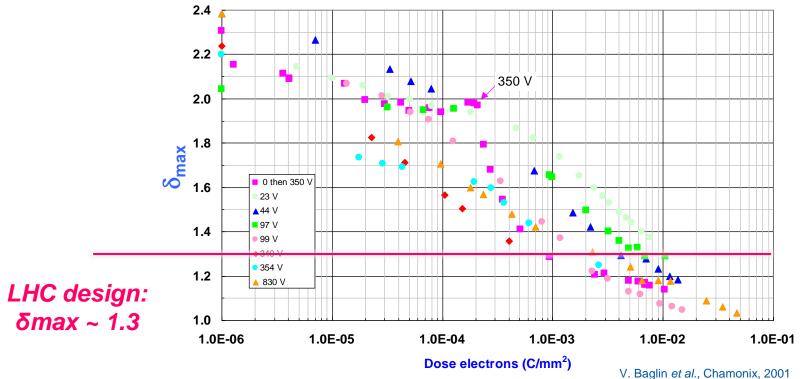
• Still under development by STFC and Dundee university, so it came too late for the LHC construction !



LHC : Scrubbing of the Surface

- Photoelectrons produced by SR are accelerated towards the test sample
- Reduction of SEY under electron irradiation is observed
- 1 to 10 mC/mm² is required
- Growth of a carbon layer (AES, XPS)



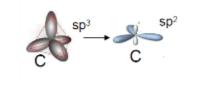




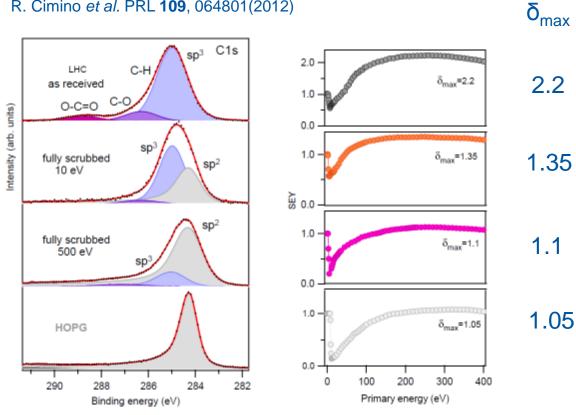
Origin of the SEY reduction at 300 K

R. Cimino et al. PRL 109, 064801(2012)

Complementary information



- Modification of C1s core level
- Conversion sp³ => sp²
- High energy electrons increase the number of graphitic like C-C bounds



HOPG : highly oriented pyrolity graphite

Graphitization of the carbon contamination layer under electron irradiation

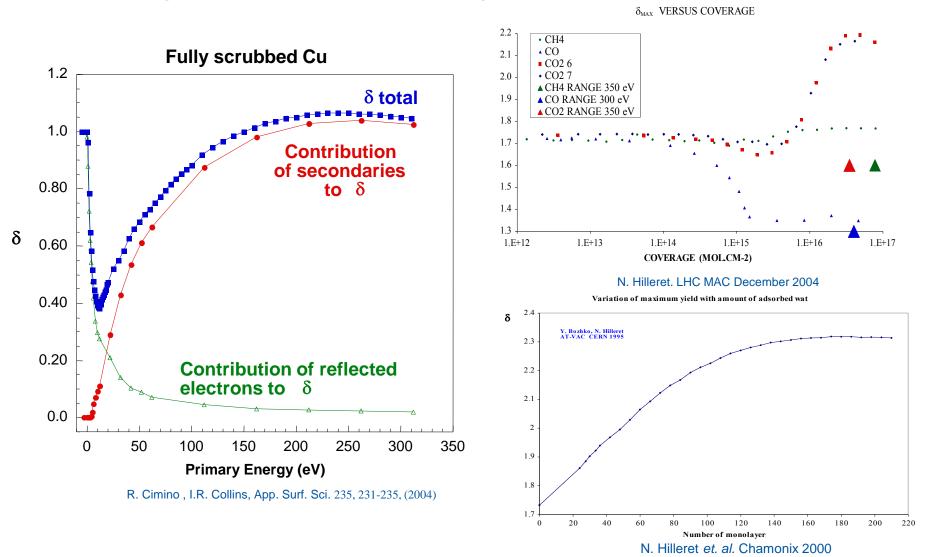


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EVC-14, Portoroz, Slovenia ,6-10 June 2016

SEY at cryogenic temperature

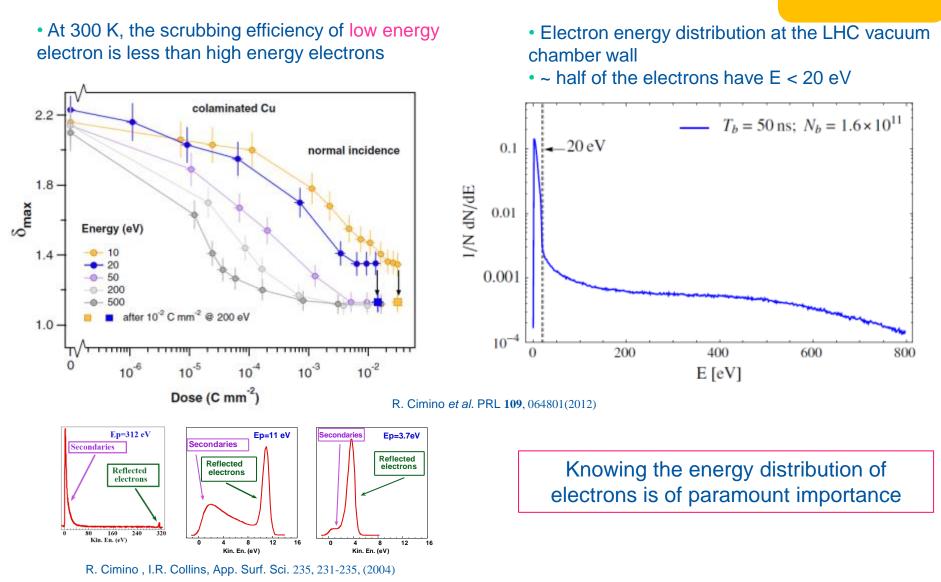
· Beam scrubbing at 10 K but SEY increases with gas condensation



CERN

Conditioning and electron energy

Complementary information



Electron desorption yield

- Unbaked copper
- Threshold around 10 eV

$$\eta(E) = \eta_0 \left(\frac{E - E_c}{300 - E_c}\right)^{0.85}$$

Table 1: Fit parameters				
	$\eta_0 / (\text{molec./e}^-)$	E_C / eV		
C_2H_6	1.1×10^{-1}	11.4		
CH_4	2.1×10^{-2}	7.5		
CO	5.8×10^{-2}	7.2		
CO_2	2.7×10^{-1}	9.1		
H_2	$1.9 imes 10^{0}$	12.7		
H_2O	3.1×10^{-2}	-22.9		

$$\eta = \frac{number \ of \ desorbed \ molecules}{incident \ electrons}$$

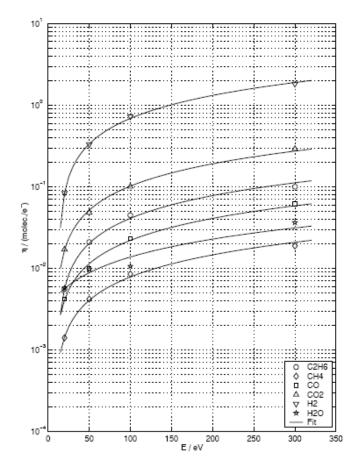


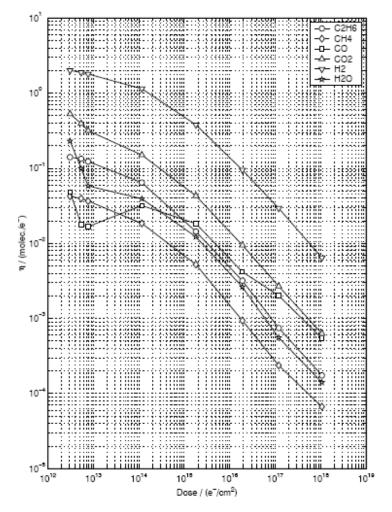
Figure 5: Electron induced desorption yield as a function of the electron energy. The values for 20, 50, and 100 eV have been obtained by interpolation between the two measurements shown in figure 4 at a constant dose of $1.4 \times 10^{14} \text{ e}^{-}/\text{cm}^{2}$.

G. Vorlaufer et al., CERN VTN, 2000



Electron dose

• Reduction of the electron desorption yield with the electron dose



$$\eta(\mathrm{D}) = \eta_0 \left(\frac{\mathrm{D}}{\mathrm{D}_0}\right)^{-\mathrm{a}}$$

	H ₂	CH ₄	H ₂ O	СО	CO ₂
η ₀	2 10 -1	2.5 10 ⁻²	1 10 ⁻¹	3.5 10 ⁻²	5 10 ⁻²
D ₀ x 10 ¹⁴	3	1	6	2	4
а	0.47	0.62	0.66	0.49	0.54

Figure 3: Effect of the electron dose on the electron induced desorption yield of an unbaked copper sample. The electron energy during bombardment and measurement was 300 eV.



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Electron scrubbing

- After a dose of ~ 5 10^{18} e/cm² *i.e.* 8 mC/mm², the maximum of SEY equals ~ 1.3
- The scrubbing process desorbs several monolayers of gas from the surface
- Potential impact on:
 - frequency of NEG activation
 - increase of SEY due to gas condensation



Unbaked Cu - ESD - 300 eV

	H ₂	CH ₄	H ₂ O	CO	CO ₂
Q x 10 ¹⁵	19	0.4	4	2	3

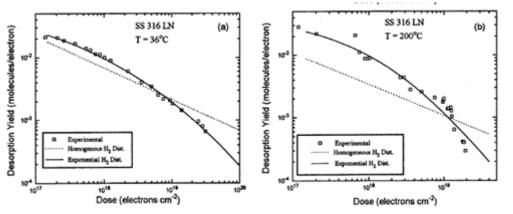
→ several monolayer of gas are desorbed when a surface is conditioned



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Electron desorption studies at different temperature

Hydrogen desorption



 H₂ electron desorption can be explained by a diffusion model with a non-uniform concentration *i.e.* H is produced by dissociation of hydroxydes under electron bombardement

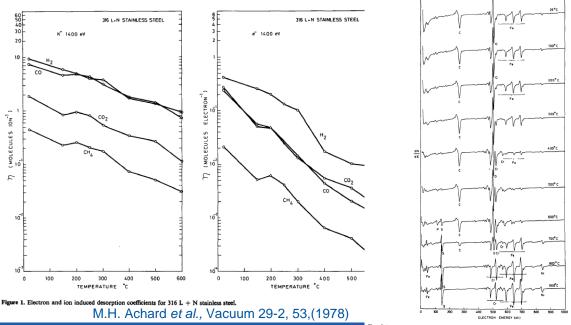
However, the diffusion coefficients taken for RT and 200°C were the same

J. Gómez-Goñi, A.G. Mathewson. J. Vac. Sci. Technol. A 15(6) (1997) 3093

• No **obvious correlation** between the surface composition determined by AES and desorption yields as a function of temperature : No changes in AES spectra vs 1 to 3 orders of magnitude decrease for the yields.

• The thickness of the oxide layer is more than 3 monolayers (AES scanning depth).

A porous surface oxide layer provide the reservoir of gas



igure 7. Auger spectra for 316 L + N stainless steel as a function of temperature.



CERN

Electron desorption at cryogenic temperature: Cu

• The yields are very large and range from 0.1 to 50

• For a monolayer (10¹⁵ molecules/cm2)

	H ₂	CH ₄	CO	CO ₂
η	500	5	10	0.5

Studied for 300 eV electrons with :

- 1) Pure gas
- 2) Equimolecular mixture of 4 gases
- 3) Standard LHC gas composition

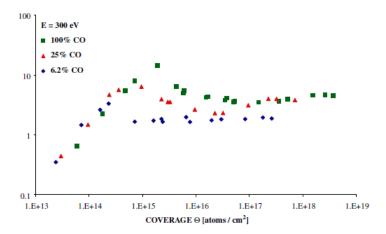


Fig. 7. The CO desorption yield as a function of CO coverage for different condensed gas composition (electron energy 300eV).

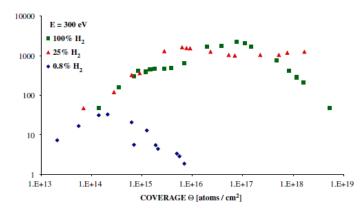


Fig. 5. The H2 desorption yield as a function of H2 coverage for different condensed gas composition (electron energy 300 eV).

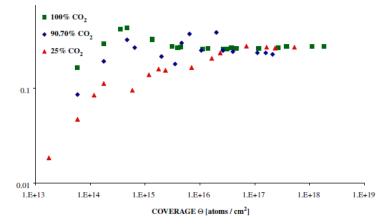


Fig. 8. The CO₂ desorption yield as a function of CO₂ coverage for different condensed gas composition (electron energy 300 eV).

H. Tratnik et al., Vacuum 81, 731,(2007)



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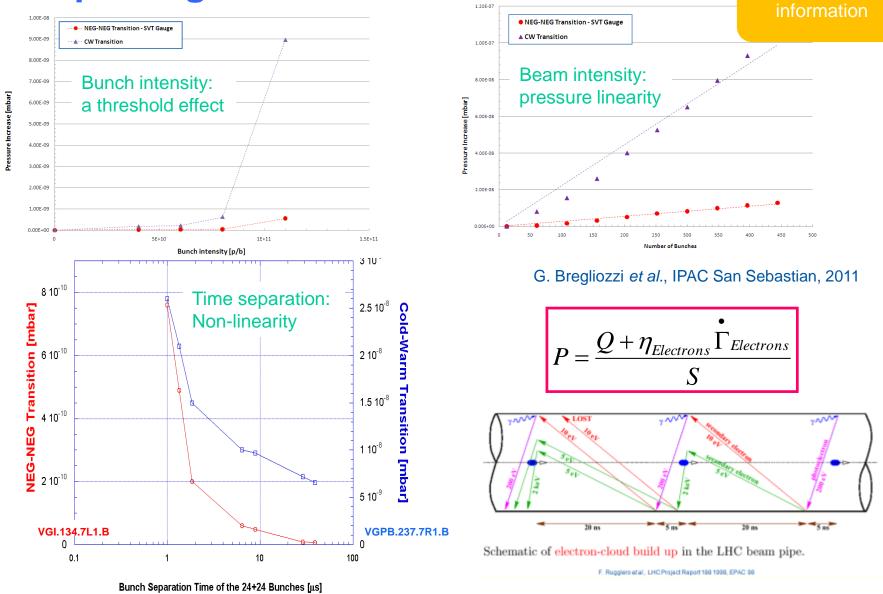
Complementary information

Beam structure



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Multipacting: Influence of Beam Structure





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Lecture 4 summary

- In accelerators, the circulating beam can contribute to stimulate molecular desorption
- Those phenomenon can lead to much larger gas load than the thermal outgassing rate
- Photon stimulated desorption originates from SR
- Ion stimulated desorption originates from beam gas ionisation and can lead to vacuum instability
- Particle losses
- Electron stimulated desorption originates from an electron cloud



Some References

- Cern Accelerator School, Vacuum technology, CERN 99-05
- Cern Accelerator School, Vacuum in accelerators, CERN 2007-03
- The physical basis of ultra-high vacuum, P.A. Redhead, J.P. Hobson, E.V. Kornelsen. AVS.
- Scientific foundations of vacuum technique, S. Dushman, J.M Lafferty. J. Wiley & sons.
 Elsevier Science.
- Les calculs de la technique du vide, J. Delafosse, G. Mongodin, G.A. Boutry. Le vide.
- Vacuum Technology, A. Roth. Elsevier Science
 Some Journals Related to Vacuum Technolgy
- Journal of vacuum science and technology
- Vacuum



Thank you for your attention !!!



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